

KSA709

High Voltage Amplifier

- Collector-Base Voltage : V_{CBO}= -160V
- Collector Power Dissipation : P_C=800mW
- Complement to KSC1009
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{CBO}	Collector-Base Voltage	-160	V
V _{CEO}	Collector-Emitter Voltage	-150	V
V _{EBO}	Emitter-Base Voltage	-8	V
I _C	Collector Current	-700	mA
P _C	Collector Power Dissipation	800	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = -100 \mu A, I_E = 0$	-160			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA, I _B =0	-150			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = -100 \mu A, I_C = 0$	-8			V
I _{CBO}	Collector Cut-off Current	V _{CB} = -100V, I _E =0			-0.1	μΑ
I _{EBO}	Emitter Cut-off Current	V_{EB} = -5V, I_{C} =0			-0.1	μΑ
h _{FE}	* DC Current Gain	V_{CE} = -2V, I_{C} = -50mA	70		400	
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	$I_C = -200 \text{mA}, I_B = -20 \text{mA}$		-0.3	-0.4	V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	I_{C} = -200mA, I_{B} = -20mA		-0.9	-1.0	V
f _T	Current Gain Bandwidth Product	V_{CE} = -10V, I_{C} = -50mA		50		MHz
C _{ob}	Output Capacitance	V _{CB} = -10V, I _E =0, f=1MHz			10	pF

^{*} Pulse Test: PW≤350µs, Duty cycle≤2%

h_{FE} Classification

Classification	0	Y	G
h _{FE}	70 ~ 140	120 ~ 240	200 ~ 400

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Typical Characteristics

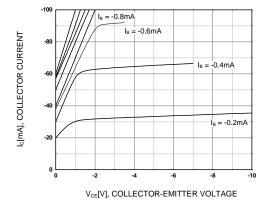


Figure 1. Static Characteristic

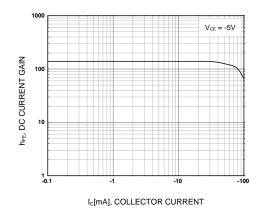


Figure 2. DC current Gain

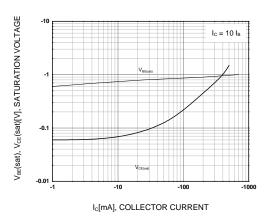


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

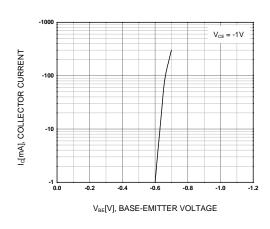


Figure 4. Base-Emitter On Voltage

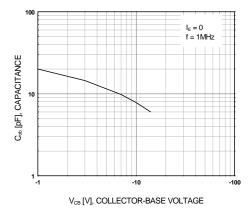
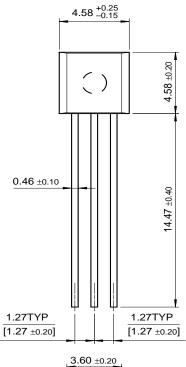


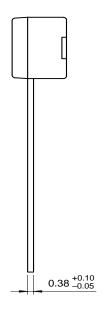
Figure 5. Collector Output Capacitance

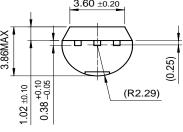
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Package Dimensions

TO-92







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